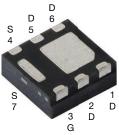
SQA444CEJW

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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET





Bottom View

Top View Marking Code: Q9XXXX

PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0390			
$R_{DS(on)} (\Omega)$ at $V_{GS} = 4.5 V$	0.0526			
I _D (A)	9			
Configuration	Single			

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- Wettable flank terminals
- 100 % R_{α} and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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ORDERING INFORMATION	
Package	PowerPAK SC-70W-6L
Lead (Pb)-free and halogen-free	SQA444CEJW

ABSOLUTE MAXIMUM RATINGS ($T_c = 25 \degree C$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	T _C = 25 °C ª	1-	9		
	T _C = 125 °C	ID	7.7		
Continuous source current (diode conduction) ^a		I _S	9	А	
Pulsed drain current ^b		I _{DM}	28		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	12.5		
Single pulse avalanche energy		E _{AS}	7.81	mJ	
Maximum power dissipation	T _C = 25 °C	PD	13.6	W	
	T _C = 125 °C	PD	4.5	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	90	°C/W	
Junction-to-case (drain)	nction-to-case (drain)		11	0/10	

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR4 material)

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70W-6L is a leadless package and features wettable flank terminals. The end of the lead terminal is plated with tin.

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SPECIFICATIONS ($T_C = 25 \ ^{\circ}C$, ur		1		[r	1	
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				-	T	1	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1	μA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V_{DS} = 60 V, T_J = 125 °C	-	-	50	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	10	-	-	А
Durain a companya ang sebata manintang sa 2		$V_{GS} = 10 V$	I _D = 4.5 A	-	0.0318	0.0390	
	D	$V_{GS} = 10 V$	I _D = 4.5 A, T _J = 125 °C	-	-	0.0623	Ω
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 4.5 A, T _J = 175 °C	-	-	0.0764	
		$V_{GS} = 4.5 V$	I _D = 3 A	-	0.0429	0.0526	
Forward transconductance b	g _{fs}	V _{DS} :	= 15 V, I _D = 4.5 A	-	17	-	S
Dynamic ^b					•	•	
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	378	530	pF
Output capacitance	Coss	$V_{GS} = 0 V$		-	215	300	
Reverse transfer capacitance	C _{rss}			-	12	17	
Total gate charge ^c	Qg		V V _{DS} = 30 V, I _D = 5 A	-	6	9	nC
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V		-	1.52	-	
Gate-drain charge ^c	Q _{gd}			-	0.55	-	
Gate resistance	R _g	f = 1 MHz		0.225	0.450	0.675	Ω
Turn-on delay time ^c	t _{d(on)}			-	8	12	
Rise time ^c	t _r	Voo	= 30 V, R_{L} = 6 Ω	-	3	6	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	13	20	ns
Fall time ^c	t _f			-	3	6	
Source-Drain Diode Ratings and Charact	eristics ^b						
Pulsed current ^a	I _{SM}			-	-	28	A
Forward voltage	V _{SD}	$I_{\rm F} = 4.5 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.84	1.2	V
Body diode reverse recovery time	t _{rr}	I _F = 2 A, di/dt = 100 A/μs		-	16	32	ns
Body diode reverse recovery charge	Q _{rr}			-	8.4	17	nC
Reverse recovery fall time	ta			-	9	-	
Reverse recovery rise time	t _b			-	7	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.0	-	А

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

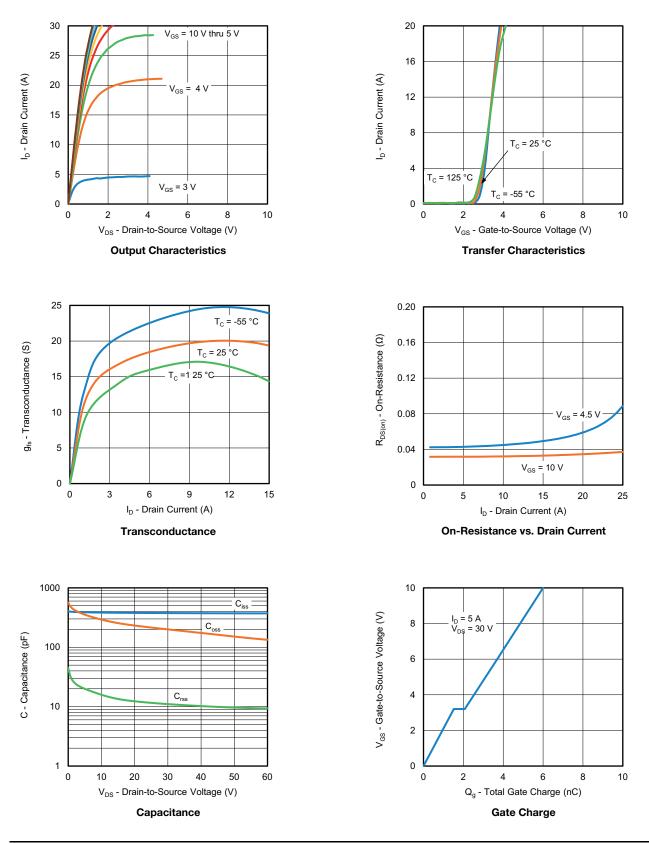
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



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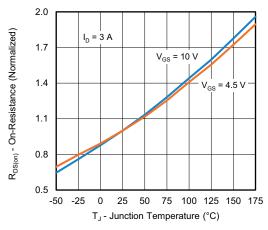
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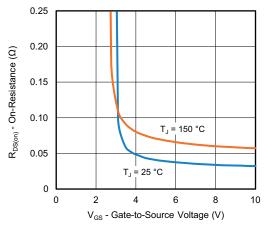


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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



On-Resistance vs. Junction Temperature



T_. = 150 °C

0.6

On-Resistance vs. Gate-to-Source Voltage

T_J = 25 °C

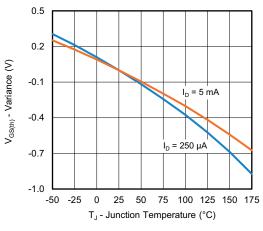
0.9

V_{SD} - Source-to-Drain Voltage (V)

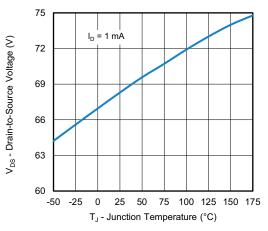
Source Drain Diode Forward Voltage

1.2

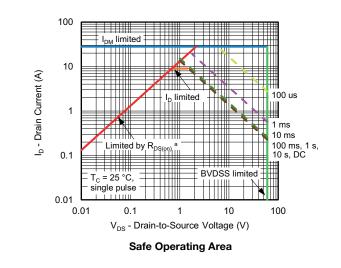
1.5



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



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0.3

100

10

1

0.1

0.01

0

I_s - Source Current (A)

4

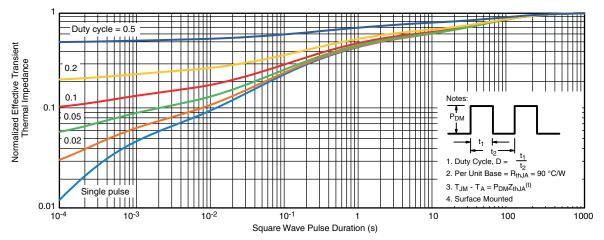
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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